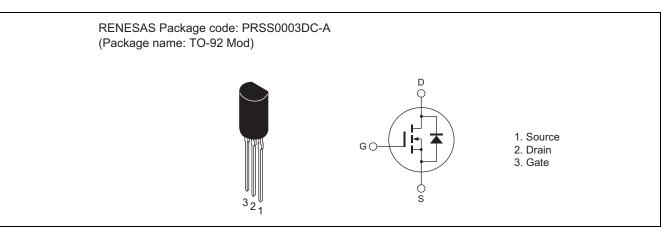


400V - 3A - MOS FET High Speed Power Switching

Features

- Low on-state resistance $R_{DS(on)} = 2.4 \ \Omega$ typ. (at $I_D = 1.5 \ A$, $V_{GS} = 10 \ V$, $Ta = 25^{\circ}C$)
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$ Value Unit Item Symbol 400 V Drain to source voltage V_{DSS} V_{GSS} ±30 V Gate to source voltage ID Note1 3 Drain current А ID(pulse) Note4 6 A Drain peak current I_{DR}^{Note1} 3 A Body-drain diode reverse drain current Note4 Body-drain diode reverse drain peak current 6 A IDR(pulse) I_{AP}^{Note3} Avalanche current 2.5 А EAR Note3 Avalanche energy 0.357 mJ Pch Note 2 W Channel dissipation 2.54 °C/W Channel to ambient thermal Impedance θch-a 49.2 Channel temperature Tch 150 °C -55 to +150 °C Storage temperature Tstg

Notes: 1. Limited by Tch max.

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Pulse width limited by safe operating area.

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Rev.2.00

Aug 03, 2012



Electrical Characteristics

						$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	400	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 400 V, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	—	±0.1	μΑ	V_{GS} = ±30 V, V_{DS} = 0
Gate to source cutoff voltage	V _{GS(off)}	3.5	—	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	2.4	2.9	Ω	I_D = 1.5 A, V_{GS} = 10 V ^{Note 5}
Input capacitance	Ciss	_	165	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	25	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	2.6	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	11	_	ns	I _D = 1.5 A
Rise time	tr	—	12	—	ns	V _{GS} = 10 V
Turn-off delay time	$t_{d(off)}$	_	23	_	ns	$R_L = 133 \Omega$
Fall time	t _f	_	20	_	ns	Rg = 10 Ω
Total gate charge	Qg	_	6.0	_	nC	V _{DD} = 320 V
Gate to source charge	Qgs	—	1.2	_	nC	V _{DS} = 100 V
Gate to drain charge	Qgd	—	3.4	_	nC	I _D = 3 A
Body-drain diode forward voltage	V _{DF}		0.9	1.5	V	$I_F = 3 \text{ A}, V_{GS} = 0^{\text{Note 5}}$
Body-drain diode reverse recovery time	t _{rr}		200		ns	$I_F = 3 A, V_{GS} = 0$
						di _F /dt = 100 A/µs

Note: 5. Pulse test

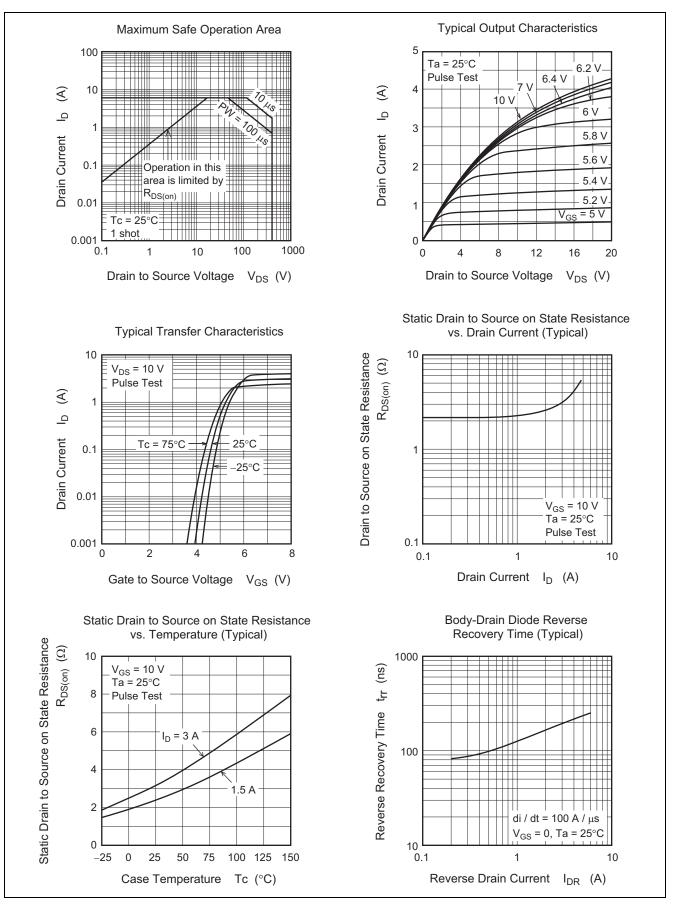
 Since this device is equipped with high voltage FET chip (V_{DSS} ≥ 400 V), high voltage may be supplied. Therefore, please be sure to confirm about electric discharge between drain terminal and other terminal.

7. This device is sensitive to electrostatic discharge.

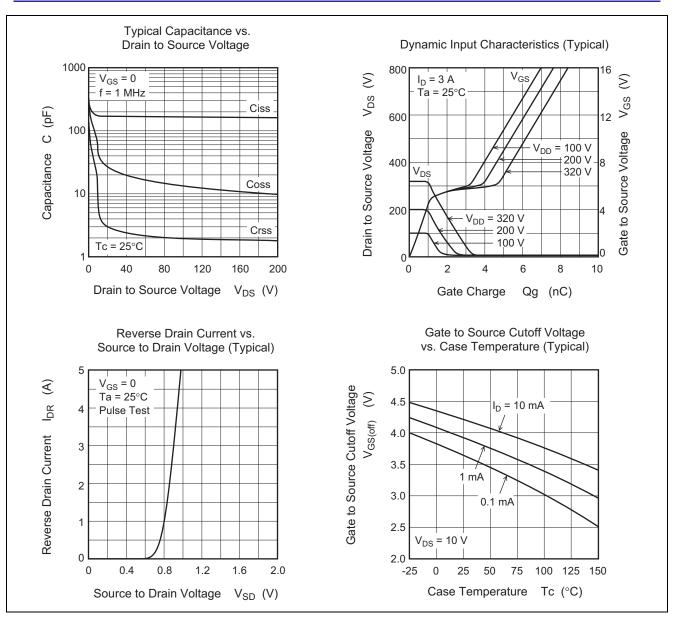
It is recommended to adopt appropriate cautions when handling this product.



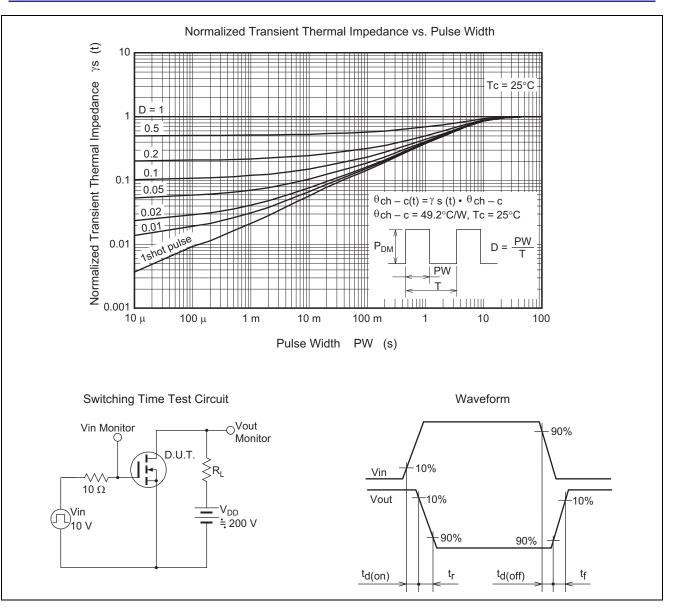
Main Characteristics





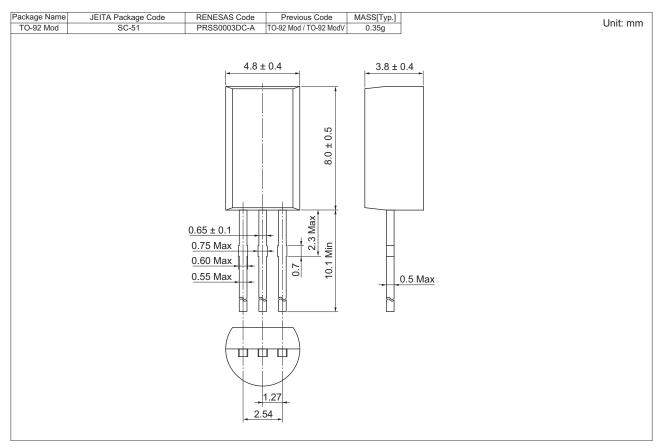






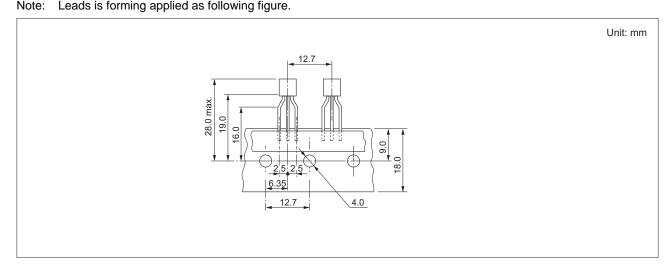


Package Dimensions



Ordering Information

Orderable Part No.	Quantity	Shipping Container				
RJK4002DJE-00#Z0	2500 pcs	Hold Box, Radial Taping				
Note: Leads is forming applied as following figure						





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